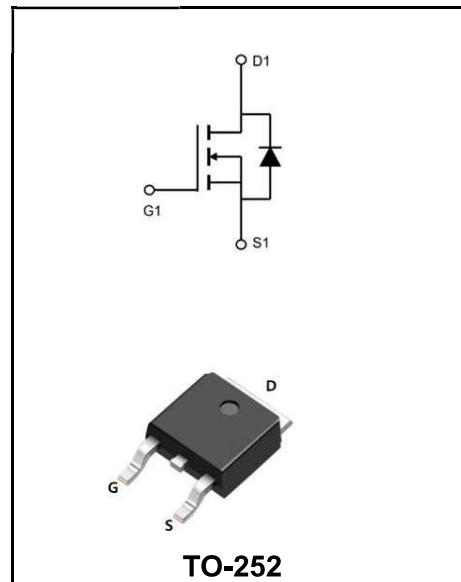


60V N-CHANNEL ENHANCEMENT MODE MOSFET
MAIN CHARACTERISTICS

| | |
|--|-------------------------------|
| I_D | 90A |
| V_{DSS} | 60V |
| R_{DS(on)-typ(@V_{GS}=10V)} | < 7.0mΩ(Type:5.8 mΩ) |


Application

- ◆ Battery protection
- ◆ Load switch
- ◆ Uninterruptible power supply

Mechanical Data

- ◆ Case: Molded plastic
- ◆ Mounting Position: Any
- ◆ Molded Plastic: UL Flammability Classification Rating 94V-0
- ◆ Solder bath temperature 275°C maximum, 10s per JESD22-106

Product Specification Classification

| Part Number | Package | Marking | Pack |
|-------------|---------|-------------|--------------|
| YFW90N06AD | TO-252 | YFW 90N06AD | 2500PCS/Tape |

Maximum Ratings at Tc=25°C unless otherwise specified

| Characteristics | Symbols | Value | Units |
|--|---------------------------------|-------------|-------|
| Drain-Source Voltage | V _{DS} | 60 | V |
| Gate - Source Voltage | V _{GS} | ±20 | V |
| Continuous Drain Current ⁽¹⁾ | I _D | 90 | A |
| Pulsed Drain Current ⁽²⁾ | I _{DM} | 320 | A |
| Diode forward current | I _S | 37 | A |
| Pulsed source current | I _{SP} | 210 | A |
| Power dissipation | P _D | 108 | W |
| Single pulsed avalanche energy ⁽³⁾ | E _{AS} | 205.4 | mJ |
| Operation and storage temperature | T _{stg} T _j | -55 to +150 | °C |
| Thermal resistance, junction-case | R _{θJC} | 1.4 | °C/W |
| Thermal Resistance Junction-Ambient ⁽⁴⁾ | R _{θJA} | 62.5 | °C/W |

Maximum Ratings at Tc=25°C unless otherwise specified

| Characteristics | Test Condition | Symbols | Min | Typ | Max | Units |
|--|---|----------------------|-----|------|------|-------|
| Drain-Source Breakdown Voltage | V _{GS} =0V, I _D =250μA | V _{(BR)DSS} | 60 | 64 | - | V |
| Zero Gate Voltage Drain Current | V _{DS} =60V, V _{GS} =0V | I _{DSS} | - | - | 1.0 | μA |
| Gate to Body Leakage Current | V _{GS} =±20V, V _{DS} =0V | I _{GSS} | - | - | ±100 | nA |
| Gate Threshold Voltage | V _{DS} =V _{GS} , I _D =250μA | V _{GS(th)} | 2.0 | 3.0 | 4.0 | V |
| Static Drain-Source on-Resistance note | V _{GS} = 10V, I _D =30A | R _{DSS(ON)} | - | 5.8 | 7.0 | mΩ |
| Input Capacitance | V _{DS} =30V V _{GS} =0V f=1.0MHz | C _{iss} | - | 4136 | - | pF |
| Output Capacitance | | C _{oss} | - | 286 | - | pF |
| Reverse Transfer Capacitance | | C _{rss} | - | 257 | - | pF |
| Total Gate Charge | V _{DS} =30V I _D =30A V _{GS} =10V | Q _g | - | 90 | - | nC |
| Gate-Source Charge | | Q _{gs} | - | 9 | - | nC |
| Gate-Drain("Miller") Charge | | Q _{gd} | - | 18 | - | nC |
| Turn-on delay time | V _{DS} =30V I _D = 30A V _{GS} =10V R _G = 1.8Ω | t _{d(on)} | - | 9 | - | nS |
| Turn-on Rise Time | | T _r | - | 7 | - | nS |
| Turn-Off Delay Time | | t _{d(OFF)} | - | 40 | - | nS |
| Turn-Off Fall Time | | t _f | - | 15 | - | nS |
| Maximum Continuous Drain to Source Diode Forward Current | I _S | - | - | 90 | - | A |
| Maximum Pulsed Drain to Source Diode Forward Current | I _{SM} | - | - | 320 | - | A |
| Drain to Source Diode Forward Voltage | V _{GS} =0V, I _S =30A | V _{SD} | - | - | 1.2 | V |
| Body Diode Reverse Recovery Time | I _F =30A, dI/dt=100A/μs | T _{rr} | - | 33 | - | nS |
| Body Diode Reverse Recovery Charge | | Q _{rr} | - | 46 | - | nC |

Note:

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
2. The data tested by pulsed , pulse width .The EAS data shows Max. rating .
3. The test cond ≤ 300us duty cycle ≤ 2%, duty cycle ition is TJ =25°C, VDD =35V, VG =10V, R G =25Ω, L=0.5mH, IAS =21A
4. The power dissipation is limited by 175°C junction temperature
5. The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Ratings and Characteristic Curves

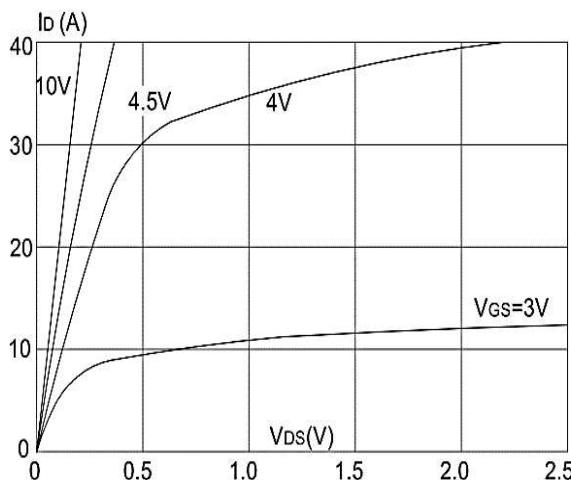


Figure 1: Output Characteristics

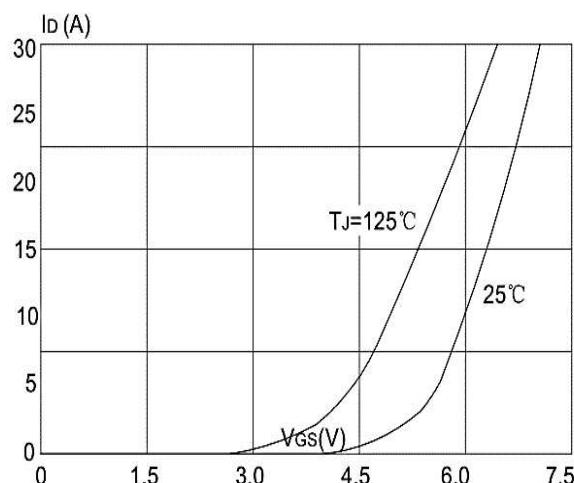


Figure 2: Typical Transfer Characteristics

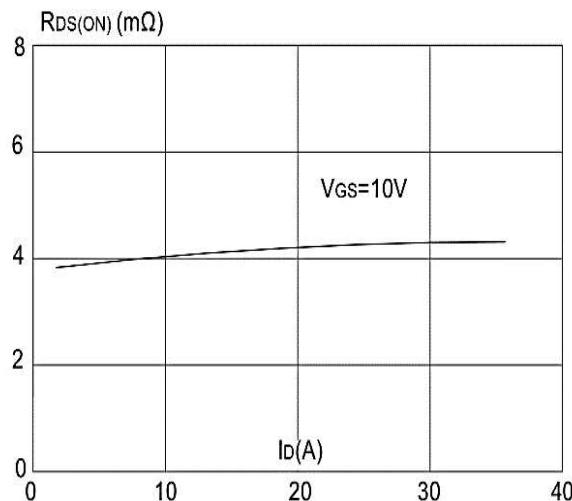


Figure 3: On-resistance vs. Drain Current

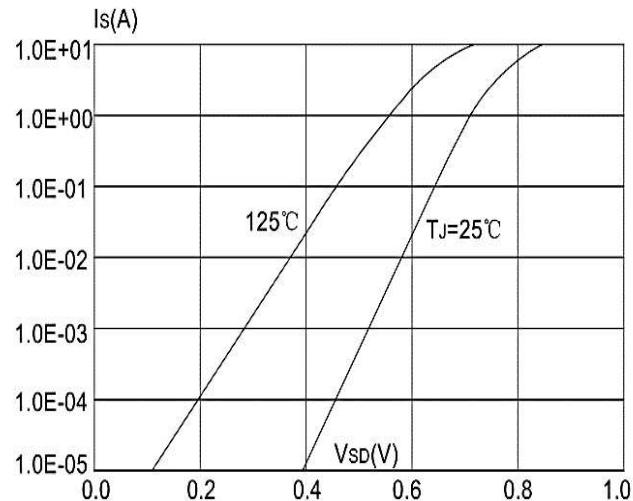


Figure 4: Body Diode Characteristics

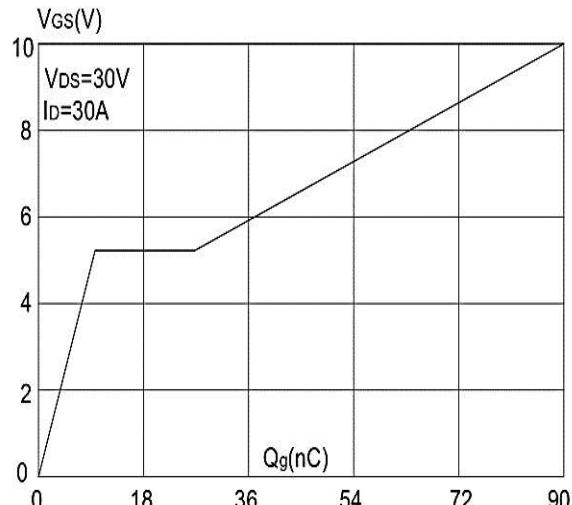


Figure 5: Gate Charge Characteristics

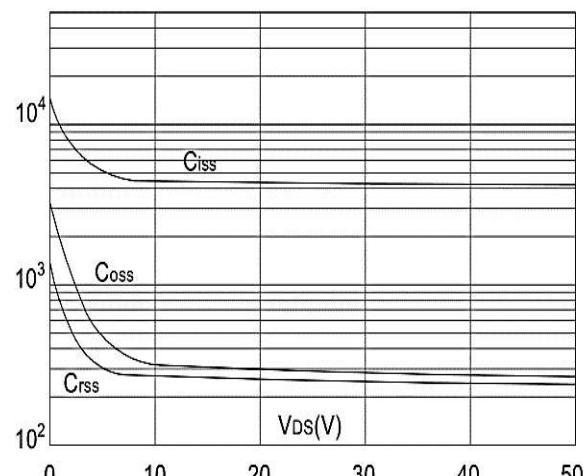


Figure 6: Capacitance Characteristics

Ratings and Characteristic Curves

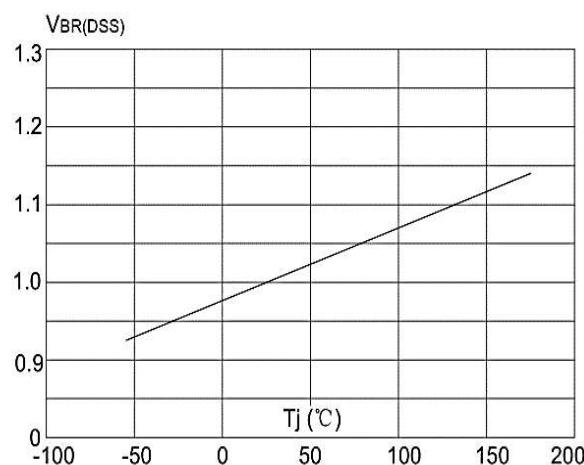


Figure 7: Normalized Breakdown Voltage vs Junction Temperature

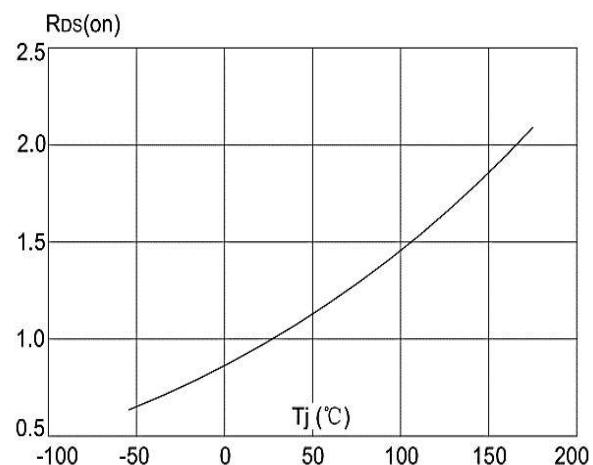


Figure 8: Normalized on Resistance vs. Junction Temperature

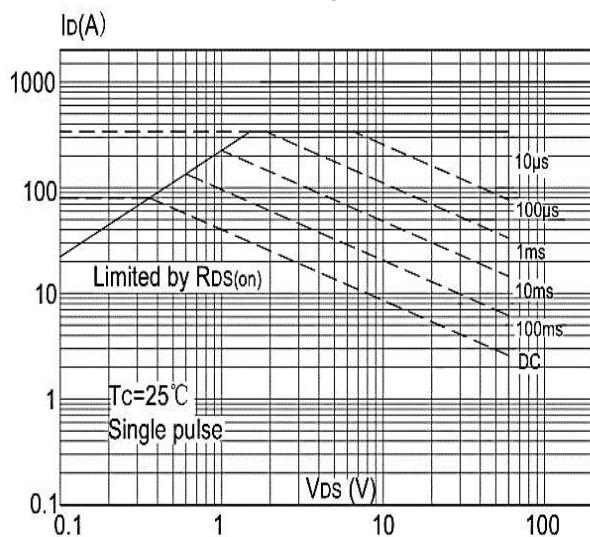


Figure 9: Maximum Safe Operating Area

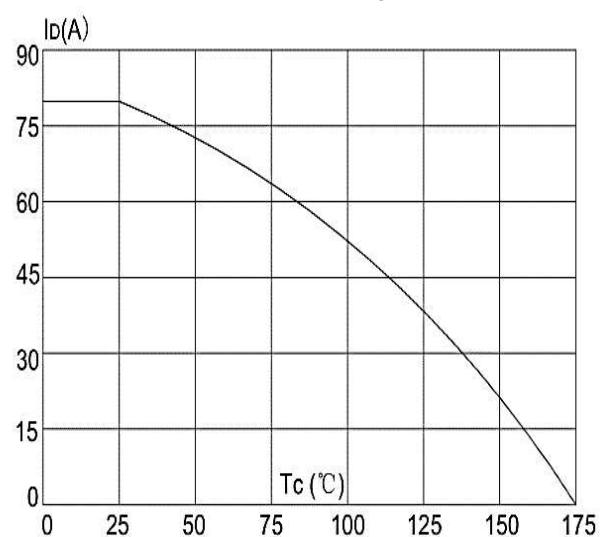


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

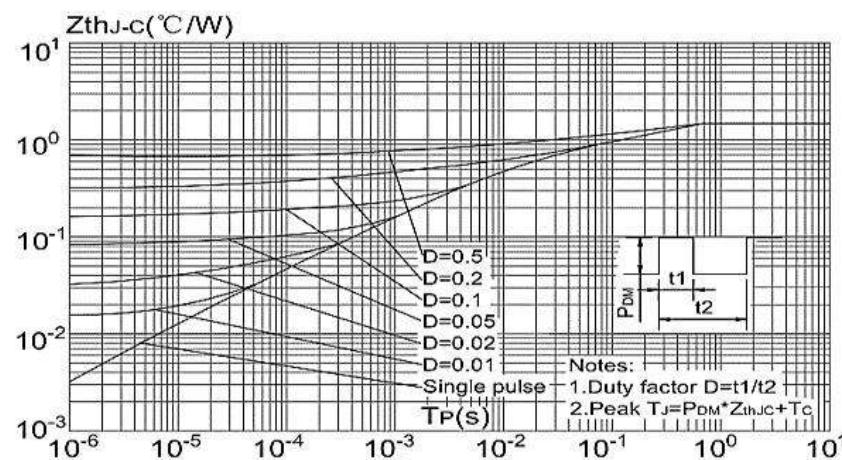
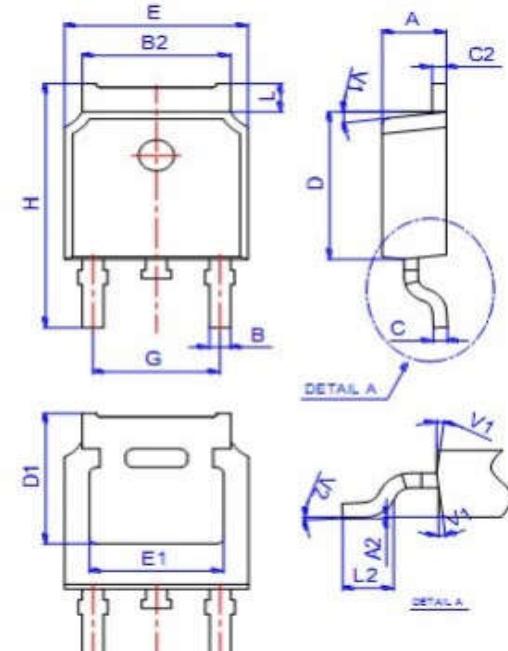


Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

Package Outline Dimensions Millimeters

TO-252



| Dim. | Min. | Typ. | Max. |
|------|---------|------|-------|
| A | 2.10 | - | 2.50 |
| A2 | 0 | - | 0.10 |
| B | 0.66 | - | 0.86 |
| B2 | 5.18 | - | 5.48 |
| C | 0.40 | - | 0.60 |
| C2 | 0.44 | - | 0.58 |
| D | 5.90 | - | 6.30 |
| D1 | 5.30REF | | |
| E | 6.40 | - | 6.80 |
| E1 | 4.63 | - | - |
| G | 4.47 | - | 4.67 |
| H | 9.50 | - | 10.70 |
| L | 1.09 | - | 1.21 |
| L2 | 1.35 | - | 1.65 |
| V1 | - | 7° | - |
| V2 | 0° | - | 6° |

All Dimensions in millimeter